# 74HC6323A; 74HCT6323A

Programmable ripple counter with oscillator; 3-state

Rev. 4 — 9 July 2018 Product data sheet

### 1 General description

The 74HC6323A; 74HCT6323A is an oscillator designed for quartz crystal combined with a programmable 3-state counter, a 3-state output buffer and an overriding asynchronous master reset ( $\overline{\text{MR}}$ ). With the two select inputs S1 and S2 the counter can be switched in the divide-by-1, 2, 4 or 8 mode. If left floating the clock is divided by 8. The oscillator is designed to operate either in the fundamental or third overtone mode depending on the crystal and external components applied. On-chip capacitors minimize external component count for third overtone crystal applications. The oscillator may be replaced by an external clock signal at input X1. In this event the other oscillator pin (X2) must be floating. The counter advances on the negative-going transition of X1. A LOW level on  $\overline{\text{MR}}$  resets the counter, stops the oscillator and sets the output buffer in the 3-state condition.  $\overline{\text{MR}}$  can be left floating since an internal pull-up resistor will make the  $\overline{\text{MR}}$  inactive.

The X1 input has CMOS input switching levels and may be driven by a TTL output using a pull-up resistor connected to  $V_{CC}$ . Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ .

#### 2 Features and benefits

- Programmable 3-stage ripple counter
- Suitable for over-tone crystal application up to 50 MHz ( $V_{CC}$  = 5 V ± 10%)
- 3-state output buffer
- Two internal capacitors
- · Recommended operating range for use with third overtone crystals 3 to 6 V
- Oscillator stop function (MR)
- Input levels:
  - For 74HC6323: CMOS level
  - For 74HCT6323: TTL level
- ESD protection:
  - HBM JESD22-A114-A exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C



## 3 Applications

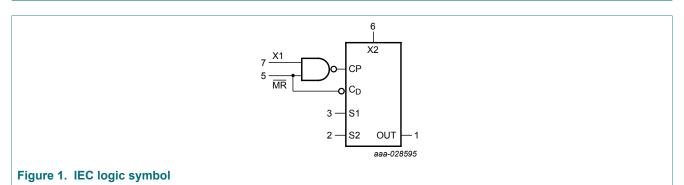
- · Control counters
- Timers
- · Frequency dividers
- · Time-delay circuits
- CIO (Compact Integrated Oscillator)
- Third-overtone crystal operation

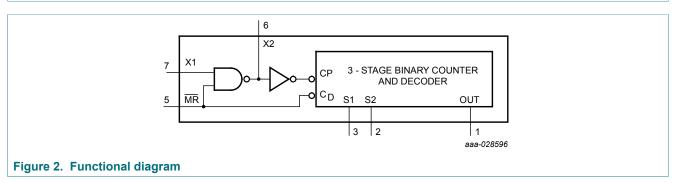
# 4 Ordering information

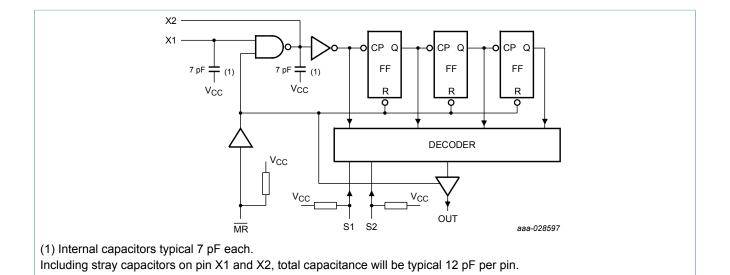
**Table 1. Ordering information** 

Type number	Package			
	Temperature range	Name	Description	Version
74HC6323AD	-40 °C to +125 °C	SO8	plastic small outline package; 8 leads;	SOT96-1
74HCT6323AD			body width 3.9 mm	

# 5 Functional diagram



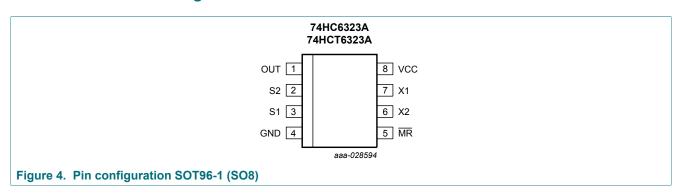




# 6 Pinning information

Figure 3. Logic diagram

### 6.1 Pinning



### 6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OUT	1	counter output
S1, S2	3, 2	mode select inputs for divide by 1, 2, 4 or 8
GND	4	ground (0 V)
MR	5	master reset input (active LOW)
X2	6	oscillator pin
X1	7	clock input /oscillator pin
V <sub>CC</sub>	8	supply voltage

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## 7 Functional description

Table 3.

Inputs		Outputs
S1	S2	OUT
0	0	f <sub>i</sub>
0	1	f <sub>i</sub> /2
1	0	f <sub>i</sub> /4
1	1	f <sub>i</sub> /8

## 8 Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
lok	output clamping current	$V_{\rm O}$ < -0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
Io	output current	OUT output; $-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±35	mA
I <sub>CC</sub>	supply current	OUT output	-	70	mA
I <sub>GND</sub>	ground current	OUT output	-70	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$ [1]	-	500	mW

<sup>[1]</sup>  $P_{tot}$  derates linearly with 8 mW/K above 70 °C.

# 9 Recommended operating conditions

#### Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	7	4HC6323	Α	74	4HCT632	CT6323A		
			Min	Тур	Max	Min	Тур	Max		
$V_{CC}$	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V	
VI	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V	
$V_{O}$	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V	
T <sub>amb</sub>	ambient temperature		-40	-	+125	-40	-	+125	°C	
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.0 V	-	-	625	-	-	-	ns/V	
		V <sub>CC</sub> = 4.5 V	-	1.67	139	-	1.67	139	ns/V	
		V <sub>CC</sub> = 6.0 V	-	-	83	-	-	-	ns/V	

### 10 Static characteristics

**Table 6. Static characteristics** 

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC63	23A									
V <sub>IH</sub>	HIGH-level input	MR, X1, S1, S2 input								
	voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input	MR, X1, S1, S2 input								
	voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output	X2 output								
	voltage	$V_{CC}$ = 4.5 V; X1 = GND; $\overline{MR}$ = $V_{CC}$ ; $I_{O}$ = -2.6 mA	3.98	-	-	3.84	-	3.7	-	V
		$V_{CC}$ = 6.0 V; X1 = GND; $\overline{MR}$ = $V_{CC}$ ; $I_{O}$ = -3.3 mA	5.48	-	-	5.34	-	5.2	-	V
		$V_{CC}$ = 4.5 V; X1 = $V_{CC}$ ; $\overline{MR}$ = GND; $I_{O}$ = -2.6 mA	3.98	-	-	3.84	-	3.7	-	V
		$V_{CC} = 6.0 \text{ V}; \text{ X1} = V_{CC}; \overline{\text{MR}} = \text{GND}; I_{O} = -3.3 \text{ mA}$	5.48	-	-	5.34	-	5.2	-	V
		$V_{CC}$ = 2.0 V; X1 = GND; $\overline{MR}$ = $V_{CC}$ ; $I_{O}$ = -20 $\mu A$	1.9	2.0	-	1.9	-	1.9	-	V
		$V_{CC}$ = 4.5 V; X1 = GND; $\overline{MR}$ = $V_{CC}$ ; $I_{O}$ = -20 $\mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$V_{CC}$ = 6.0 V; X1 = GND; $\overline{MR}$ = $V_{CC}$ ; $I_{O}$ = -20 $\mu A$	5.9	6.0	-	5.9	-	5.9	-	V
		$V_{CC}$ = 2.0 V; X1 = $V_{CC}$ ; $\overline{MR}$ = GND; $I_{O}$ = -20 $\mu A$	1.9	2.0	-	1.9	-	1.9	-	V
		$V_{CC}$ = 4.5 V; X1 = $V_{CC}$ ; $\overline{MR}$ = GND; $I_{O}$ = -20 $\mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$V_{CC} = 6.0 \text{ V}; \text{ X1} = V_{CC}; \overline{MR} = \text{GND}; I_{O} = -20 \mu\text{A}$	5.9	6.0	-	5.9	-	5.9	-	V

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
V <sub>OH</sub>	HIGH-level output	OUT output; $V_I = V_{IH}$ or $V_{IL}$								
	voltage	$V_{CC} = 2.0 \text{ V}; I_{O} = -20 \mu\text{A}$	1.9	2.0	-	1.9	-	1.9	-	V
		V <sub>CC</sub> = 4.5 V; I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$V_{CC} = 6.0 \text{ V}; I_{O} = -20 \mu\text{A}$	5.9	6.0	-	5.9	-	5.9	-	V
		$V_{CC} = 4.5 \text{ V}; I_{O} = -6 \text{ mA}$	3.98	-	-	3.84	-	3.7	-	V
		$V_{CC} = 6.0 \text{ V}; I_{O} = -7.8 \text{ mA}$	5.48	-	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW level output	X2 output								
	voltage	$V_{CC} = 4.5 \text{ V}; \text{ X1} = V_{CC}; \overline{MR} = V_{CC}; I_{O} = 2.6 \text{ mA}$	-	-	0.26	-	0.33	-	0.4	V
		$V_{CC} = 6.0 \text{ V}; \text{ X1} = V_{CC}; \overline{MR} = V_{CC}; I_0 = 3.3 \text{ mA}$	-	-	0.26	-	0.33	-	0.4	V
		$V_{CC} = 2.0 \text{ V}; \text{ X1} = V_{CC}; \overline{MR} = V_{CC}; I_0 = 20 \mu\text{A}$	-	0.0	0.1	-	0.1	-	0.1	V
		$V_{CC} = 4.5 \text{ V}; \text{ X1} = V_{CC}; \overline{MR} = V_{CC}; I_{O} = 20 \mu\text{A}$	-	0.0	0.1	-	0.1	-	0.1	V
		$V_{CC} = 6.0 \text{ V}; \text{ X1} = V_{CC}; \overline{MR} = V_{CC}; I_0 = 20 \mu\text{A}$	-	0.0	0.1	-	0.1	-	0.1	V
$V_{OL}$	LOW level output	OUT output; $V_I = V_{IH}$ or $V_{IL}$								
	voltage	$V_{CC} = 2.0 \text{ V; } I_{O} = 20  \mu\text{A}$	-	0.0	0.1	-	0.1	-	0.1	V
		$V_{CC} = 4.5 \text{ V}; I_{O} = 20 \mu\text{A}$	-	0.0	0.1	-	0.1	-	0.1	V
		$V_{CC} = 6.0 \text{ V}; I_{O} = 20 \mu\text{A}$	-	0.0	0.1	-	0.1	-	0.1	V
		V <sub>CC</sub> = 4.5 V; I <sub>O</sub> = 6 mA	-		0.26	-	0.33	-	0.4	V
		$V_{CC} = 6.0 \text{ V}; I_{O} = 7.8 \text{ mA}$	-	-	0.26	-	0.33	-	0.4	V
lį	input leakage current	X1 input; $V_{CC}$ = 6.0 V; $\overline{MR}$ = $V_{CC}$ ; S1 = $V_{CC}$ ; S2 = $V_{CC}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>pu</sub>	pull-up current	$\overline{MR}$ , S1 and S2 inputs; $V_{CC}$ = 6.0 V; $V_{I}$ = GND; see Figure 13 and Figure 14.	-5	-30	-100	-	-	-	-	μΑ
I <sub>CC</sub>	supply current	$V_{CC} = 6.0 \text{ V}; V_{I} = V_{CC} \text{ or GND}; I_{O} = 0 \text{ A}$	-	-	8	-	80	-	160	μA
Cı	input capacitance	MR, S1 and S2 inputs	-	3.5	-	-	-	-	-	pF

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HCT6	323A			1	1	,		1	'	
$V_{IH}$	HIGH-level input	$\overline{\rm MR}$ , S1 and S2 inputs; V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
	voltage	X1 input								
		V <sub>CC</sub> = 4.5 V	3.15	-	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>	LOW-level input	$\overline{MR}$ , S1 and S2 inputs; $V_{CC}$ = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
	voltage	X1 input								
		V <sub>CC</sub> = 4.5 V	-	-	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V <sub>OH</sub>	HIGH-level output	X2 output; V <sub>CC</sub> = 4.5 V								
	voltage	X1 = GND; $\overline{MR}$ = $V_{CC}$ ; $I_O$ = -2.6 mA	3.98	-	-	3.84	-	3.7	-	V
		$X1 = V_{CC}$ ; $\overline{MR} = GND$ ; $I_0 = -2.6 \text{ mA}$	3.98	-	-	3.84	-	3.7	-	V
		X1 = GND; $\overline{MR}$ = V <sub>CC</sub> ; I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		X1 = $V_{CC}$ ; $\overline{MR}$ = GND; $I_O$ = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		OUT output; V <sub>CC</sub> = 4.5 V; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -6 mA	3.98	-	-	3.84	-	3.7	-	V
$V_{OL}$	LOW-level output	X2 output; $V_{CC}$ = 4.5 V; X1 = $V_{CC}$ ; $\overline{MR}$ = $V_{CC}$								
	voltage	I <sub>O</sub> = 2.6 mA	-	-	0.26	-	0.33	-	0.4	V
		Ι <sub>Ο</sub> = 20 μΑ	-	0.0	0.1	-	0.1	-	0.1	V
		OUT output; $V_{CC}$ = 4.5 V; $V_I$ = $V_{IH}$ or $V_{IL}$								
		I <sub>O</sub> = 20 μA	-	0.0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 6 mA	-	-	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	X1 input; $V_{CC}$ = 5.5 V; $\overline{MR}$ = $V_{CC}$ ; S1 = $V_{CC}$ ; S2 = $V_{CC}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>pu</sub>	pull-up current	$\overline{MR}$ , S1 and S2 inputs; $V_{CC} = 5.5 \text{ V}$ ; $V_{I} = GND$ ; see Figure 13 and Figure 14.	-5	-25	-100	-	-	-	-	μΑ

Symbol	Parameter	Conditions		25 °C		-40 °C to	+85 °C	-40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
I <sub>CC</sub>	supply current	$V_{CC} = 5.5 \text{ V}; V_{I} = V_{CC} \text{ or GND}; I_{O} = 0 \text{ A}$	-	-	8	-	80	-	160	μΑ
$\Delta I_{CC}$	additional supply current	$\overline{MR}$ , S1 and S2 inputs; $V_{CC}$ = 5.5 V; $V_I$ = $V_{CC}$ or GND; other inputs at $V_{CC}$ or GND; $I_O$ = 0 A	-	40	144	-	180	-	196	μA
Cı	input capacitance	MR, S1 and S2 inputs	-	3.5	-	-	-	-	-	pF

# 11 Dynamic characteristics

**Table 7. Dynamic characteristics** 

GND = 0 V;  $C_L$  = 50 pF unless otherwise specified; for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			°C to 5 °C		C to 5 °C	Unit
74HC63	22 A		Min	Тур	Max	Min	Max	Min	Max	
t <sub>pd</sub>	propagation delay	X1 to OUT divide by 1; S1 = GND; S2 = GND; see Figure 5								
		V <sub>CC</sub> = 2.0 V	_	61	185	_	230	_	275	ns
		V <sub>CC</sub> = 4.5 V	-	22	37	-	46	-	55	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	17	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	19	31	-	39	-	47	ns
		X1 to OUT divide by 2; S1 = GND; S2 = V <sub>CC</sub> ; see <u>Figure 5</u>								
		V <sub>CC</sub> = 2.0 V	-	74	235	-	290	-	350	ns
		V <sub>CC</sub> = 4.5 V	_	27	47	-	58	-	70	ns
		V <sub>CC</sub> = 6.0 V	-	23	40	-	49	-	60	ns
		X1 to OUT divide by 4; S1 = V <sub>CC</sub> ; S2 = GND; see <u>Figure 5</u>								
		V <sub>CC</sub> = 2.0 V	-	91	285	-	355	-	425	ns
		V <sub>CC</sub> = 4.5 V	-	33	57	-	71	-	85	ns
		V <sub>CC</sub> = 6.0 V	-	28	48	-	60	-	72	ns
		X1 to OUT divide by 8; S1 = V <sub>CC</sub> ; S2 = V <sub>CC</sub> ; see <u>Figure 5</u>								
		V <sub>CC</sub> = 2.0 V	-	105	335	-	415	-	500	ns
		V <sub>CC</sub> = 4.5 V	-	38	67	-	83	-	100	ns
		V <sub>CC</sub> = 6.0 V	-	32	57	-	71	-	85	ns
t <sub>PZL</sub>	OFF-state	MR to OUT; see Figure 6								
	to LOW propagation	V <sub>CC</sub> = 2.0 V	-	36	150	-	185	-	225	ns
	delay	V <sub>CC</sub> = 4.5 V	_	13	30	-	37	_	45	ns
		V <sub>CC</sub> = 6.0 V	-	11	26	-	31	-	38	ns
t <sub>PZH</sub>	OFF-state	MR to OUT; see Figure 6 [2]								
	to HIGH propagation	V <sub>CC</sub> = 2.0 V	-	61	200	-	250	-	300	ns
	delay	V <sub>CC</sub> = 4.5 V	-	22	40	-	50	-	60	ns
		V <sub>CC</sub> = 6.0 V	-	19	34	-	43	-	51	ns
t <sub>dis</sub>	disable time	MR to OUT; see Figure 6 [3]								
		V <sub>CC</sub> = 2.0 V	-	75	150	-	185	-	225	ns
		V <sub>CC</sub> = 4.5 V	-	15	30	-	37	-	60 51 225 45	ns
		V <sub>CC</sub> = 6.0 V	-	13	26	-	31	-	38	ns

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Symbol	Parameter	Conditions		25 °C			°C to		°C to 5 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
t <sub>t</sub>	transition	OUT; see Figure 5								
	time	V <sub>CC</sub> = 2.0 V	-	14	60	-	75	-	90	ns
		V <sub>CC</sub> = 4.5 V	_	5	12	-	15	-	19	ns
		V <sub>CC</sub> = 6.0 V	-	4	10	-	13	-	15	ns
t <sub>W</sub>	pulse width	X1 HIGH or LOW; see Figure 5								
		V <sub>CC</sub> = 2.0 V	50	17	-	60	-	75	-	ns
		V <sub>CC</sub> = 4.5 V	10	6	-	12	-	15	-	ns
		V <sub>CC</sub> = 6.0 V	9	5	-	10	-	13	-	ns
		MR LOW; see Figure 7								
		V <sub>CC</sub> = 2.0 V	80	22	-	100	_	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	8	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	7	-	17	-	20	-	ns
t <sub>rec</sub>	recovery	MR to X1; see Figure 7								
	time	V <sub>CC</sub> = 2.0 V	100	19	-	125	-	150	-	ns
		V <sub>CC</sub> = 4.5 V	20	7	-	25	-	30	-	ns
		V <sub>CC</sub> = 6.0 V	17	6	-	21	-	26	-	ns
f <sub>max</sub>	maximum	X1; see Figure 5								
	frequency	V <sub>CC</sub> = 2.0 V	10	17	-	8	-	6.6	-	MHz
		V <sub>CC</sub> = 4.5 V	50	85	-	40	-	33	-	MHz
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	90	-	-	-	-	-	MHz
		V <sub>CC</sub> = 6.0 V	59	100	-	47	-	39	-	MHz
C <sub>PD</sub>	power dissipation capacitance	An external clock is applied to X1 with: $t_r = t_f \le 6$ ns, $V_l = GND$ to $V_{CC}$ , $\overline{MR} = HIGH$								
		divide by 1; S1 = GND; S2 = GND	-	54	-	-	-	-	-	pF
		divide by 2; S1 = GND; S2 = V <sub>CC</sub>	-	42	-	-	-	-	-	pF
		divide by 4; S1 = V <sub>CC</sub> ; S2 = GND	-	36	-	-	-	-	-	pF
		divide by 8; S1 = $V_{CC}$ ; S2 = $V_{CC}$	-	33	-	-	-	-	-	pF

Symbol	Parameter	Conditions		25 °C			°C to 5 °C		°C to 5 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
<b>74HCT6</b>	323A									
t <sub>pd</sub>	propagation delay	X1 to OUT divide by 1; S1 = GND; S2 = GND; see <u>Figure 5</u>	[1]							
		V <sub>CC</sub> = 45 V	-	24	40	-	50	-	60	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	17	-	-	-	-	-	ns
		X1 to OUT divide by 2; S1 = GND; S2 = V <sub>CC</sub> ; see <u>Figure 5</u>								
		V <sub>CC</sub> = 4.5 V	-	29	50	-	62	-	75	ns
		X1 to OUT divide by 4; S1 = V <sub>CC</sub> ; S2 = GND; see <u>Figure 5</u>								
		V <sub>CC</sub> = 4.5 V	-	35	60	-	75	-	90	ns
		X1 to OUT divide by 8; S1 = $V_{CC}$ ; S2 = $V_{CC}$ ; see <u>Figure 5</u>								
		V <sub>CC</sub> = 4.5 V	-	40	70	-	87	-	105	ns
t <sub>PZL</sub>	OFF-state	MR to OUT; see Figure 6								
	to LOW propagation delay	V <sub>CC</sub> = 4.5 V	-	16	30	-	37	-	45	ns
t <sub>PZH</sub>	OFF-state	MR to OUT; see Figure 6	[2]							
	to HIGH propagation delay	V <sub>CC</sub> = 4.5 V	-	22	38	-	47	-	57	ns
t <sub>dis</sub>	disable time	MR to OUT; see Figure 6	[3]							
		V <sub>CC</sub> = 4.5 V	-	21	35	-	43	-	52	ns
t <sub>t</sub>	transition	OUT; see Figure 5	[4]							
	time	V <sub>CC</sub> = 4.5 V	-	5	12	-	15	-	19	ns
t <sub>W</sub>	pulse width	X1 HIGH or LOW; see Figure 5								
		V <sub>CC</sub> = 4.5 V	10	6	-	12	-	15	-	ns
		MR LOW; see Figure 7								
		V <sub>CC</sub> = 4.5 V	16	8	-	20	-	24	-	ns
t <sub>rec</sub>	recovery	MR to X1; see Figure 7								
	time	V <sub>CC</sub> = 4.5 V	24	12	-	30	-	36	-	ns
f <sub>max</sub>	maximum	X1; see Figure 5								
	frequency	V <sub>CC</sub> = 4.5 V	50	85	-	40	-	33	-	MHz
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	90	-	-	-	-	-	MHz

Symbol	Parameter	er Conditions		25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit
				Тур	Max	Min	Max	Min	Max	
C <sub>PD</sub>	power dissipation capacitance	An external clock is applied to X1 with: $t_r = t_f \le 6$ ns, $V_i = GND$ to $V_{CC}$ , $\overline{MR} = HIGH$								
		divide by 1; S1 = GND; S2 = GND	-	54	-	-	-	-	-	pF
		divide by 2; S1 = GND; S2 = V <sub>CC</sub>	-	42	-	-	-	-	-	pF
		divide by 4; S1 = V <sub>CC</sub> ; S2 = GND	-	36	-	-	-	-	-	pF
		divide by 8; S1 = V <sub>CC</sub> ; S2 = V <sub>CC</sub>	-	33	-	-	-	-	-	pF

 $t_{pd}$  is the same as  $t_{PHL}$  and  $t_{PLH}.$   $t_{PZH}$  only applicable in the divide-by-1 mode and X1 must be HIGH.

 $t_{\text{dis}}$  is the same as  $t_{\text{PLZ}}$  and  $t_{\text{PHZ}}.$ 

 $t_t$  is the same as  $t_{\text{THL}}$  and  $t_{\text{TLH}}$ .

[5]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + (C_L \times V_{CC}^2 \times f_o) + (I_{pull-up} \times V_{CC})$  where:

 $f_i$  = input frequency in MHz;

 $f_0$  = output frequency in MHz;

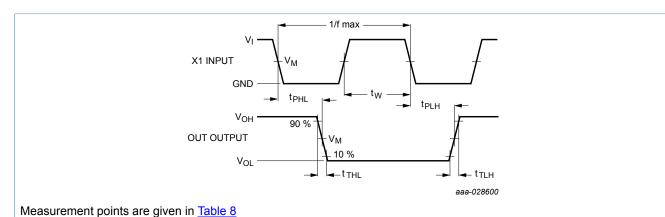
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

 $I_{pull-up}$  = pull-up currents in  $\mu A$ .

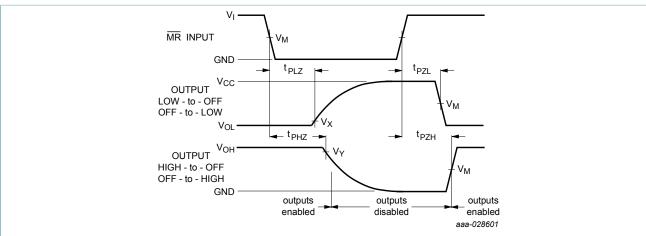
 $I_{pull\text{-}up}$  is the summation of -I  $_{I}$  (µA) of S1 and S2 inputs at the LOW state.

#### 11.1 Waveforms and test circuit



V<sub>OL</sub> and V<sub>OH</sub> are typical voltage output levels that occur with the output load.

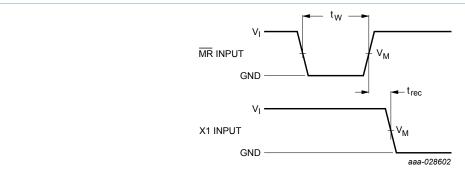
Figure 5. The clock (X1) to output (OUT) propagation delays, the clock pulse width, the output transition times and the maximum clock frequency.



Measurement points are given in Table 8

 $\ensuremath{V_{\text{OL}}}$  and  $\ensuremath{V_{\text{OH}}}$  are typical voltage output levels that occur with the output load.

Figure 6. The input MR to output OUT, 3-state enable and disable times



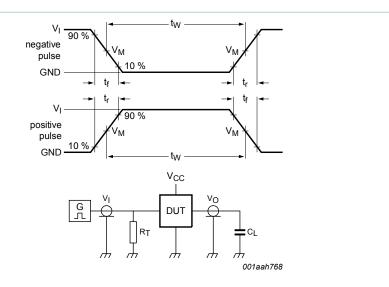
Measurement points are given in Table 8

V<sub>OL</sub> and V<sub>OH</sub> are typical voltage output levels that occur with the output load.

Figure 7. The  $\overline{\text{MR}}$  minimum pulse width and  $\overline{\text{MR}}$  to X1 recovery time.

Table 8. Measurement points

Туре	Input		Output		
	V <sub>I</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
74HC6323A	GND to V <sub>CC</sub>	0.5 x V <sub>CC</sub>	0.5 x V <sub>CC</sub>	0.1 x V <sub>CC</sub>	0.9 x V <sub>CC</sub>
74HCT6323A	GND to 3 V	1.3 V	1.3 V	0.1 x V <sub>CC</sub>	0.9 x V <sub>CC</sub>



Test data is given in Table 9.

Definitions test circuit:

 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

Figure 8. Test circuit for measuring switching times

Table 9. Test data

Туре	Input	Load	
	VI	t <sub>r</sub> , t <sub>f</sub>	CL
74HC6323A	GND to V <sub>CC</sub>	6 ns	15 pF, 50 pF
74HCT6323A	GND to 3 V	6 ns	15 pF, 50 pF

# 12 Application information

#### 12.1 Typical Crystal Oscillator

In Figure 9, R2 is the power limiting resistor. For starting and maintaining oscillation a minimum transconductance is necessary, so R2 should not be too large. A practical value for R2 is  $2.2 \text{ k}\Omega$ .

The oscillator has been designed to operate over a wide frequency spectrum, for quartz crystals operating in the fundamental mode and in the overtone mode. The circuit is a Pierce type oscillator and requires a minimum of external components. There are two on-chip capacitors, X1 and X2, of approximately 7 pF. Together with the stray and input capacitance the value becomes 12 pF for 8-pin SO packages. These values are convenient and make it possible to run the oscillator in the third overtone without external capacitors applied. If a certain frequency is chosen, the IC parameters, as forward transconductance, and the crystal parameters such as the motional resistances R1 (fundamental), R3 (third overtone) and R5 (fifth overtone), are of paramount importance. Also the values of the external components as  $R_{\rm s}$  (series resistance) and the crystal load capacitances play an important role. Especially in overtone mode oscillations,  $R_{\rm b}$  (bias resistance) and the load capacitance values are very important.

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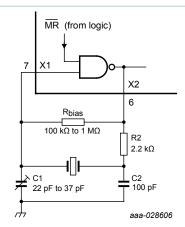
#### 12.2 Considerations for Fundamental Oscillator:

In the fundamental oscillator mode, the  $R_b$  has only the function of biasing the inverter stage, so that it operates as an amplifier with a phase shift of approximately  $180^\circ$ . The value must be high, i.e.  $100~k\Omega$  up to  $10~M\Omega$ . The load capacitors C1 and C2, must have a value that is suitable for the crystal being used. The crystal is designed for a certain frequency having a specific load capacitance. C1 can be used to trim the oscillation frequency. The series resistance reduces the total loop gain. One function of it is therefore to reduce the power dissipation in the crystal.  $R_s$  also suppresses overtone oscillations and introduces a phase shift over a broad frequency range. This is of less concern provided  $R_s$  is not too high a value.

**Note:** A combination of a small load capacitor value and a small series resistance, may cause a third overtone oscillation.

#### 12.3 Considerations for Third-overtone Oscillator:

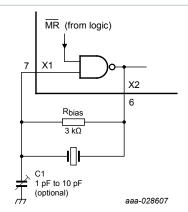
In the overtone configuration, series resistance is no longer applied. This is essential otherwise the gain for third overtone can be too small for oscillation. A simple solution to suppress the fundamental oscillation, is to spoil the crystal fundamental activity. By dramatically reducing the value of the bias resistor of the inverting stage, and applying small load capacitors, it is possible to have an insufficient phase in the total loop for fundamental oscillation. However the phase for third overtone is good. It can be explained by the  $R_b \times C_l$  time constant. During oscillation the crystal with the load capacitors cause a phase shift of  $180^\circ$ . Because  $R_b$  is parallel with the crystal (no  $R_s$ ),  $R_b$  spoils the phase for fundamental.  $R_b \times C_l$  must be of a value, that it is not spoiling the phase for third overtone too much. Because third overtone is a 3 times higher frequency than the fundamental, the  $R_b \times C_l$  cannot 'maintain' the higher third overtone frequency, which results in a less spoiled overtone phase.



Above 5 MHz replace R2 by a capacitor of half the value of C2.

 $C_L$  at which a crystal is specified (or adjusted) equals for this application C1 x C2/(C1 + C2)

Figure 9. Typical setup for a crystal oscillator operating in the fundamental mode (1 MHz to 25 MHz)

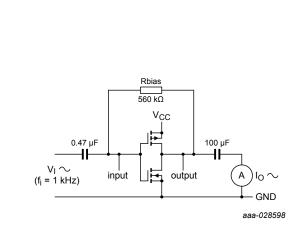


Applicable for third overtone crystals (lower damping resistance at the third harmonic frequency) at typical 50 MHz. For lower frequencies extra load capacitors must be supplied, or increase bias resistor.

Figure 10. Typical set-up for a crystal oscillator operating in the third overtone mode without the use of an inductor

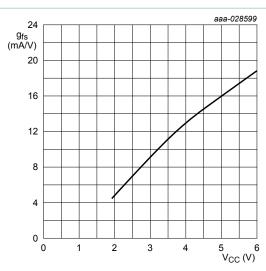
Table 10. Typical application values

Fundamental m	ode		Third overtone mode			
f (MHz)	R2 (kΩ)	C1 (pF)	C2 (pF)	f (MHz)	R <sub>bias</sub> (kΩ)	C1 (pF)
1	4.7	47 to 68 47 to 68				
10	2.2			50	3.0	4.7
25	1	33	33			



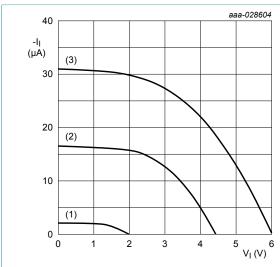
 $g_{fs} = \Delta I_O / \Delta V_I$  at  $v_O$  is constant (see Figure 12) and  $\overline{MR} = HIGH$ .

Figure 11. Test set-up for measuring forward transconductance



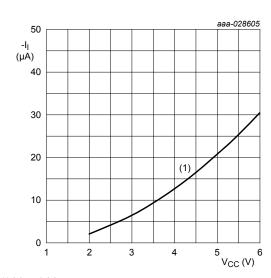
 $g_{fs}$  as a function of the supply voltage  $V_{CC}$  at  $T_{amb}$  = 25  $^{\circ}C.$ 

Figure 12. Typical forward transconductance



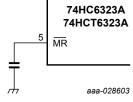
- (1)  $V_{CC} = 2 V$
- (2)  $V_{CC} = 4.3 \text{ V}$
- (3)  $V_{CC} = 6 V$

Figure 13. Typical input pull-up current as a function of the input voltage



 $(1) V_{I} = 0 V$ 

Figure 14. Typical input pull-up current as a function of the supply voltage  $(V_{CC})$ 



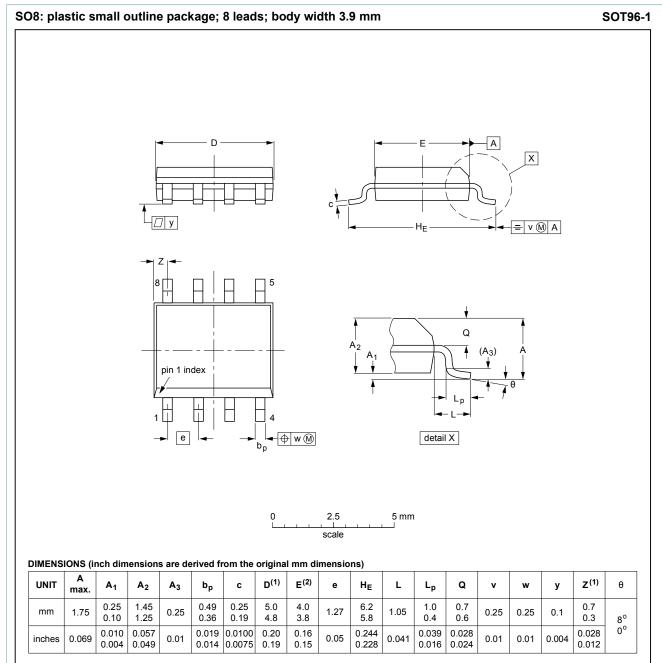
The input pull-up current is used to create a power-on delay time at  $\overline{MR}$ .

Figure 15. Power-on reset

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## 13 Package outline



#### Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT96-1	076E03	MS-012			<del>99-12-27</del> 03-02-18	

Figure 16. Package outline SOT96-1 (SO8)

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### 14 Abbreviations

#### Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

# 15 Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74HC_HCT6323A v.4	20180709	Product data sheet	-	74HC_HCT6323A v.3		
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
74HC_HCT6323A v.3	19930901	Product specification	-	74HC_HCT6323A v.2		
74HC_HCT6323A v.2	19901201	Product specification	-	74HC_HCT6323A v.1		

### 16 Legal information

#### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# 74HC6323A; 74HCT6323A

### Programmable ripple counter with oscillator; 3-state

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